Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A method for making micromechanical structures having at least one lateral gap therebetween, the method comprising:

providing a substrate;

surface micromachining the substrate to form a first capacitively-driven, lateral micromechanical structure having a first vertical sidewall and a sacrificial spacer layer on the first vertical sidewall;

forming a second micromechanical structure a first capacitive transducer electrode on the substrate, the second micromechanical structure first capacitive transducer electrode including a second vertical sidewall separated from the first vertical sidewall by the spacer layer; and

removing the spacer layer to form a first lateral <u>submicron capacitive</u> gap between the <u>first and second</u> micromechanical <u>structures</u> <u>structure and the first capacitive</u> <u>transducer electrode to increase electromechanical coupling therebetween</u>.

- 2. (currently amended) The method as claimed in claim 1 wherein the step of surface micromachining further forms a third vertical sidewall on the first micromechanical structure with the sacrificial spacer layer thereon and wherein the method further comprises forming a third micromechanical structure second capacitive transducer electrode including a fourth vertical sidewall separated from the third vertical sidewall by the spacer layer and wherein the step of removing further forms a second lateral submicron gap between the first and third micromechanical structures structure and the second capacitive transducer electrode.
 - 3. (cancel)

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4. (currently amended) The method as claimed in claim 3 1 wherein the first micromechanical structure includes a resonator and wherein the first lateral submicron capacitive gap is an electrode-to-resonator capacitive gap.

- 5. (currently amended) The method as claimed in claim 1 wherein the step of forming includes the step of plating metal on the substrate and wherein the <u>first capacitive</u> transducer electrode second micromechanical structure is a plated metal electrode.
- 6. (currently amended) The method as claimed in claim 5 further comprising preventing metal from being plated on the first micromechanical structure.
 - 7. (cancel)
 - 8. 22. (canceled)
- 23. (currently amended) The method as claimed in claim $\frac{3}{2}$ wherein the step of forming includes the step of growing the <u>first capacitive transducer</u> electrode via selective epoxy epitaxial growth.
- 24. (currently amended) The method as claimed in claim $3\ \underline{1}$ wherein the step of forming includes the steps of depositing polysilicon and etching the polysilicon to form the <u>first capacitive transducer</u> electrode.
 - 25. 26. (canceled)